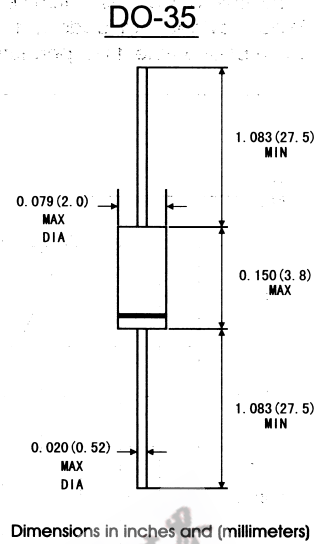


#### FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

#### MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



#### ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C )

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50°C	P <sub>tot</sub>	500 <sup>1)</sup>	mW
Junction temperature	T <sub>J</sub>	175	°C
Storage temperature range	T <sub>STG</sub>	-65 to + 175	°C

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

#### ELECTRICAL CHARACTERISTICS(TA=25°C )

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R <sub>θJA</sub>			300 <sup>1)</sup>	K/W
Forward voltage at I <sub>F</sub> =100mA	V <sub>F</sub>			1	V

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



**BXZ55... SILICON PLANAR ZENER DIODES**

Type	Zener Voltage Range <sup>1)</sup>			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
	V <sub>ZNOM</sub>	I <sub>ZT</sub> for V <sub>ZT</sub> 2)		r <sub>Zjt</sub> and r <sub>Zjk</sub> at I <sub>Zk</sub>			I <sub>R</sub> and I <sub>R2</sub> at V <sub>R</sub>			TK <sub>VZ</sub>
	V	mA	V	Ω	Ω	mA	μA	μA	V	%/K
BZX 55/C 0V8 3)	0.8		0.73.0.83	<8	<50		-	-	-	-0.26...-0.23
BZX 55/C 2V0	2.0		1.9.2.1				<100	<200		-0.09..-0.06
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100		
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50		
BZX 55/C 3V0	3		2.8.3.2	<85			<4			-0.08..-0.05
BZX 55/C 3V3	3.3		3.1.3.5		<600			<40		
BZX 55/C 3V6	3.6		3.4.3.8				<2	<40		
BZX 55/C 3V9	3.9		3.7.4.1							-0.06..-0.03
BZX 55/C 4V3	4.3		4.0.4.6	<75			<1	<20		
BZX 55/C 4V7	4.7		4.4.5.0	<60			<0.5	<10		
BZX 55/C 5V1	5.1		4.8.5.4	<35	<550					-0.02..+0.02
BZX 55/C 5V6	5.6		5.2.6.0	<25	<450					-0.05..+0.05
BZX 55/C 6V2	6.2	5	5.8.6.6	<10	<200	1			2.0	0.03.0.06
BZX 55/C 6V8	6.8		6.4.7.2	<8	<150				3.0	0.03.0.07
BZX 55/C 7V5	7.5		7.0.7.9	<7					5.0	0.03.0.07
BZX 55/C 8V2	8.2		7.7.8.7	<7	<50				6.2	0.03.0.08
BZX 55/C 9V1	9.1		8.5.9.6	<10					6.8	0.03.0.09
BZX 55/C 10	10		9.4.10.6	<15	<70		<0.1	<2	7.5	0.03.0.1
BZX 55/C 11	11		10.4.11.6	<20	<70				8.2	0.03.0.11
BZX 55/C 12	12		11.4.12.7	<20	<90				9.1	
BZX 55/C 13	13		12.4.14.1	<26	<110				10.0	
BZX 55/C 15	15		13.8.15.6	<30	<110				11.0	
BZX 55/C 16	16		15.3.17.1	<40	<170				12	
BZX 55/C 18	18		16.8.19.1	<50	<170				13	
BZX 55/C 20	20		18.8.21.2	<55	<220				15	



**BZX55... SILICON PLANAR ZENER DIODES**

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<2	16	0.04.0.12
BZX 55/C 24	24		22.8.25.6	<80				18	
BZX 55/C 27	27		25.1.28.9	<80				20	
BZX 55/C 30	30		28.32					22	
BZX 55/C 33	33		31.35					24	
BZX 55/C 36	36		34.38					27	
BZX 55/C 39	39	2.5	37.41	<500	0.5	<0.1	<5	30	
BZX 55/C 43	43		40.46	<500			33		
BZX 55/C 47	47		44.50	<600			36		
BZX 55/C 51	51		48.54	<700			39		
BZX 55/C 56	56		52.60	<700			43		
BZX 55/C 62	62		58.66	<1000			47		
BZX 55/C 68	68		64.72				51		
BZX 55/C 75	75		70.79				56		
BZX 55/C 82	82		77.87				<1500	62	
BZX 55/C 91	91		1	85.96			<2000	0.1	<10
BZX 55/C 100	100	94.106		<5000	75				
BZX 55/C 110	110	104.116		<5000	82				
BZX 55/C 120	120	114.127		<5500	91				
BZX 55/C 130	130	124.141		<6000	100				
BZX 55/C 150	150	138.156		<6500	110				
BZX 55/C 160	160	153.171		<7000	120				
BZX 55/C 180	180	168.191		<8500	130				
BZX 55/C 200	200	188.212		<10000	150				

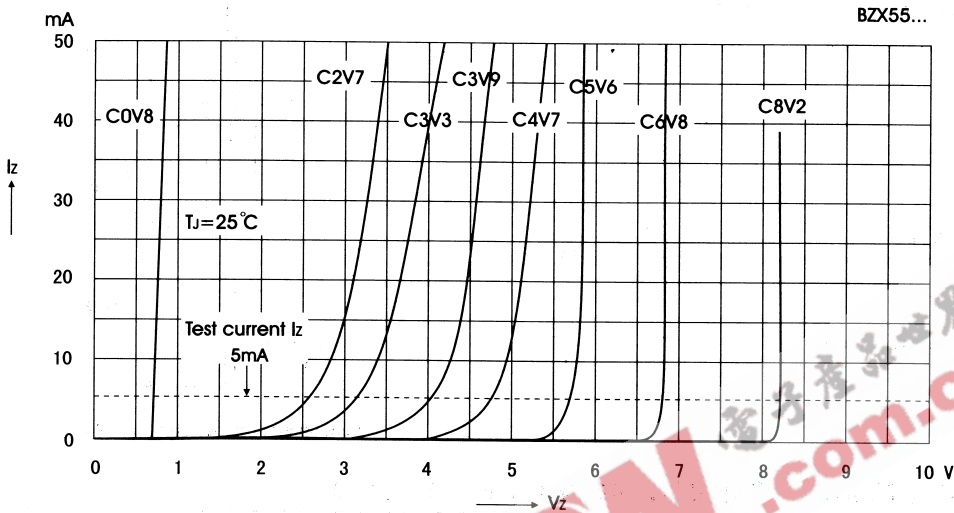
1) Tested with pulses  $t_p=20ms$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

**BXZ55... SILICON PLANAR ZENER DIODES**

**BREAKDOWN CHARACTERISTICS AT T<sub>J</sub>=CONSTANT(PULSED)**



**BREAKDOWN CHARACTERISTICS AT T<sub>J</sub>=CONSTANT(PULSED)**

